MJ14001 (PNP), MJ14002* (NPN), MJ14003* (PNP)

*Preferred Devices

High-Current Complementary Silicon Power Transistors

Designed for use in high-power amplifier and switching circuit applications.

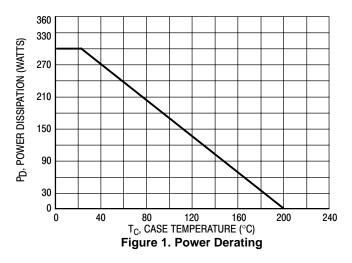
Features

- High Current Capability I_C Continuous = 60 Amperes
- DC Current Gain $-h_{FE} = 15-100$ @ I_C = 50 Adc
- Low Collector–Emitter Saturation Voltage – $V_{CE(sat)} = 2.5$ Vdc (Max) @ $I_C = 50$ Adc
- Pb–Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	MJ14001 MJ14002/03	V _{CEO}	60 80	Vdc
Collector-Base Voltage	MJ14001 MJ14002/03	V _{CBO}	60 80	Vdc
Emitter-Base Voltage		V _{EBO}	5.0	Vdc
Collector Current – Continu	ous	Ι _C	60	Adc
Base Current – Continuous		Ι _Β	15	Adc
Emitter Current – Continuou	S	Ι _Ε	75	Adc
Total Power Dissipation @ T Derate Above 25°C	_C = 25°C	PD	300 1.71	W W/∘C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	-65 to +200	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

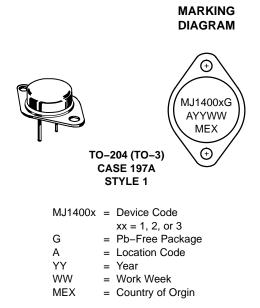




ON Semiconductor®

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60 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60-80 VOLTS, 300 WATTS



ORDERING INFORMATION

Device	Package	Shipping
MJ14001	TO-3	100 Units/Tray
MJ14001G	TO–3 (Pb–Free)	100 Units/Tray
MJ14002	TO-3	100 Units/Tray
MJ14002G	TO–3 (Pb–Free)	100 Units/Tray
MJ14003	TO-3	100 Units/Tray
MJ14003G	TO-3 (Pb-Free)	100 Units/Tray

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJ14001 (PNP), MJ14002* (NPN), MJ14003* (PNP)

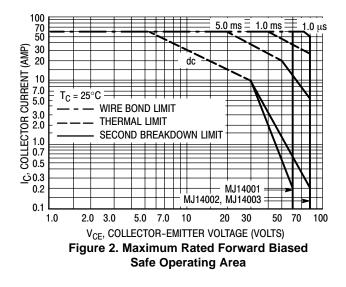
THERMAL CHARACTERISTICS

Characteristic		Max	Unit
Thermal Resistance, Junction-to-Case		0.584	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 200 \text{ mAdc}, I_B = 0$)	MJ14001 MJ14002, MJ14003	V _{CEO(sus)}	60 80		Vdc
Collector Cutoff Current $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$	MJ14001 MJ14402, MJ14003	I _{CEO}		1.0 1.0	mA
Collector Cutoff Current $(V_{CE} = 60 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ V})$ $(V_{CE} = 80 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ V})$	MJ14001 MJ14002, MJ14003	ICEX		1.0 1.0	mA
Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 80 \text{ Vdc}, I_E = 0)$	MJ14001 MJ14002, MJ14003	I _{CBO}		1.0 1.0	mA
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$)		I _{EBO}	-	1.0	mA
ON CHARACTERISTICS					
DC Current Gain (Note 1) $(I_C = 25 \text{ Adc}, V_{CE} = 3.0 \text{ V})$ $(I_C = 50 \text{ Adc}, V_{CE} = 3.0 \text{ V})$ $(I_C = 60 \text{ Adc}, V_{CE} = 3.0 \text{ V})$		h _{FE}	30 15 5.0	_ 100 _	-
		V _{CE(sat)}	_ _ _	1.0 2.5 3.0	Vdc
$\begin{array}{l} \text{Base-Emitter Saturation Voltage (Note 1)} \\ (I_{C} = 25 \text{ Adc}, I_{B} = 2.5 \text{ Adc}) \\ (I_{C} = 50 \text{ Adc}, I_{B} = 5.0 \text{ Adc}) \\ (I_{C} = 60 \text{ Adc}, I_{B} = 12 \text{ Adc}) \end{array}$		V _{BE(sat)}	_ _ _	2.0 3.0 4.0	Vdc
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)		C _{ob}	-	2000	pF

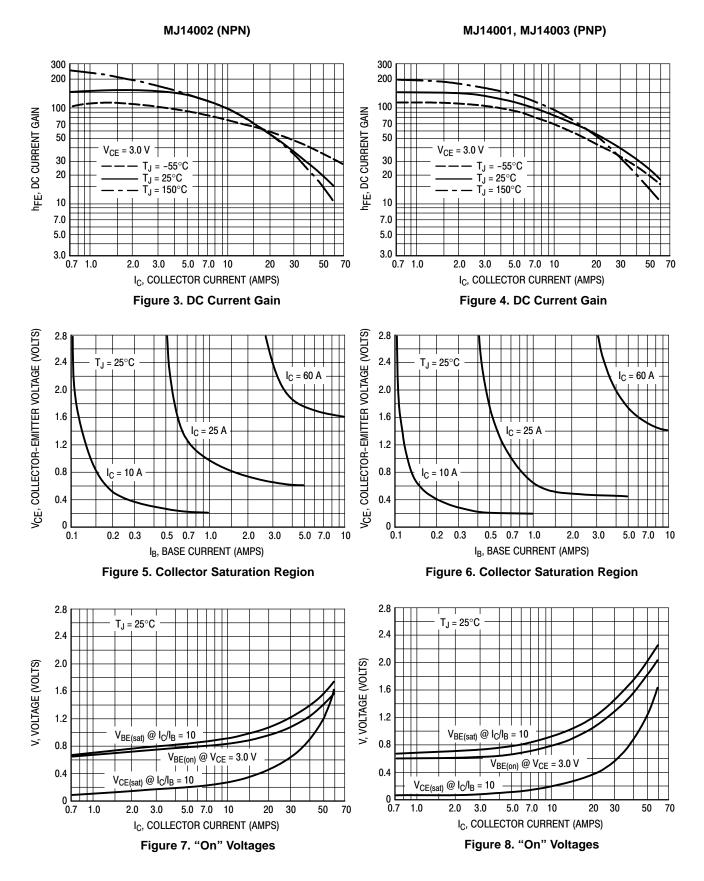
1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation: i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_{J(pk)} = 200^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 200^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

TYPICAL ELECTRICAL CHARACTERISTICS



MJ14001 (PNP), MJ14002* (NPN), MJ14003* (PNP)

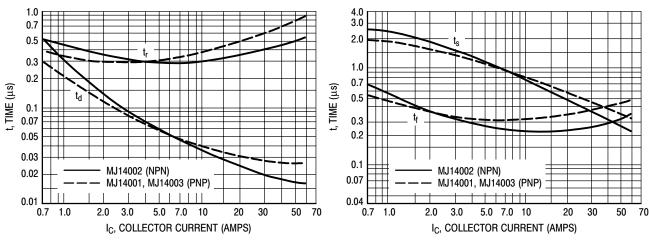


Figure 9. Turn–On Switching Times

Figure 10. Turn–Off Switching Times

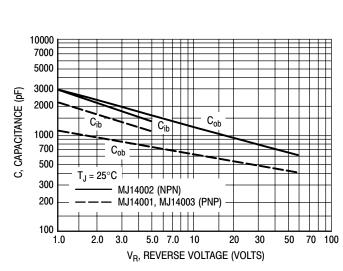
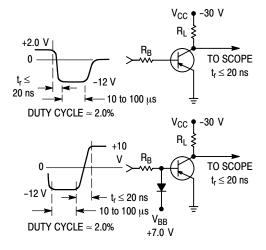


Figure 11. Capacitance Variation



FOR CURVES OF FIGURES 3 & 6, ${\sf R}_B$ & ${\sf R}_L$ are varied. Input levels are approximately as shown. For NPN CIRCUITS, reverse all polarities.



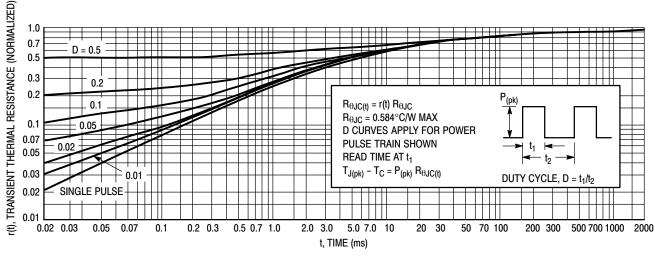
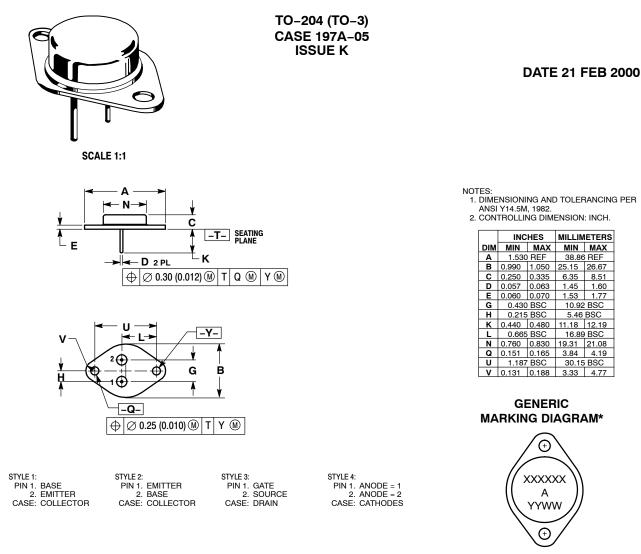


Figure 13. Thermal Response





XXXXX = Specific Device Code A = Assembly Locationa YY = Year

WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking.

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